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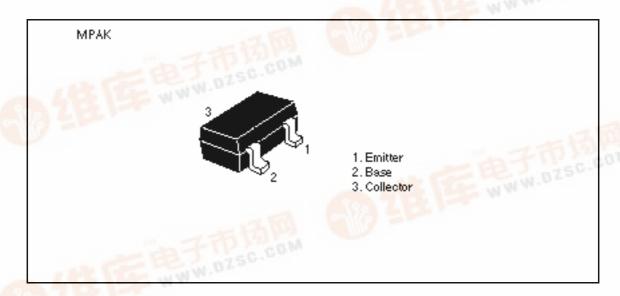
Silicon NPN Epitaxial

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Application

- UHF frequency converter
- Local oscillator, wide band amplifier

Outline





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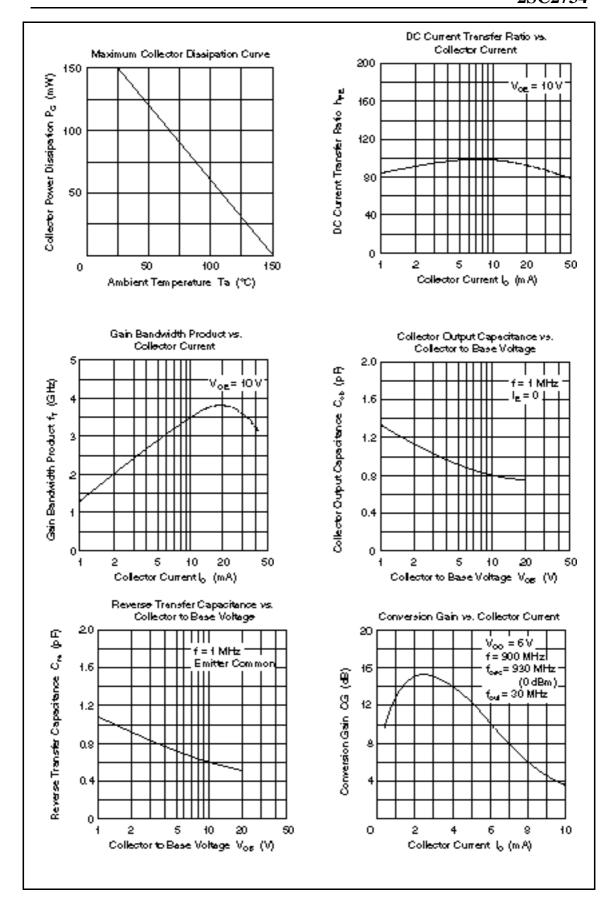
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	20	V
Collector to emitter voltage	V _{CEO}	11	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

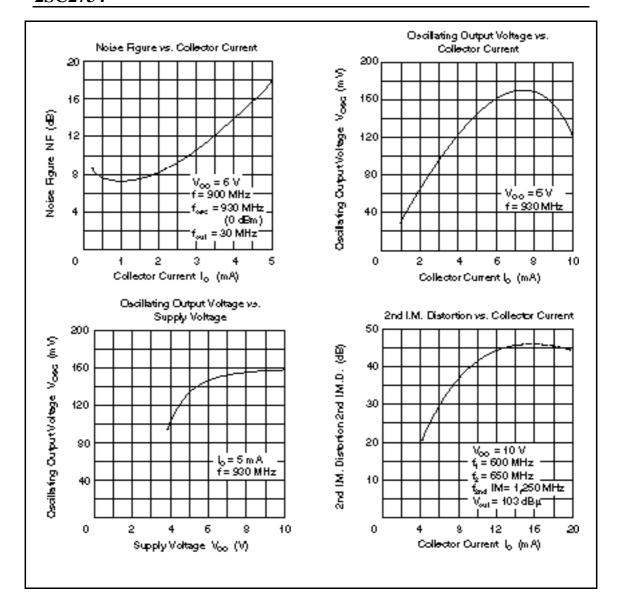
Electrical Characteristics ($Ta = 25^{\circ}C$)

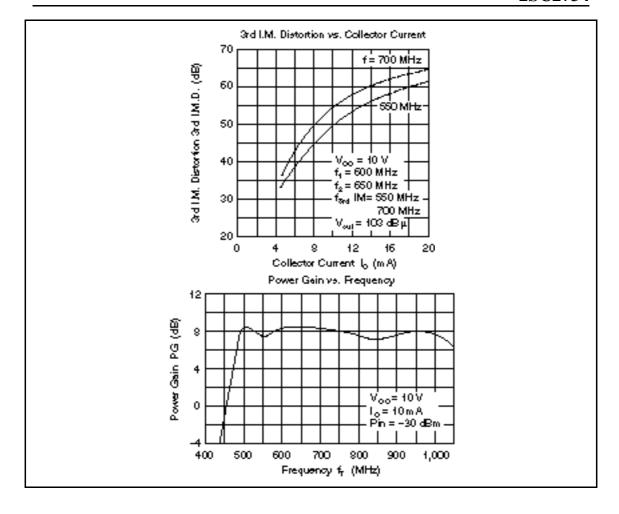
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	_	_	V	$I_{C} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	11	_	_	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	3	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μA	$V_{CB} = 10 \text{ V}, I_{E} = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	_	_	0.7	V	$I_C = 10 \text{ mA}, I_B = 5 \text{ mA}$
DC current transfer ratio	h _{FE}	20	90	200		$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$
Gain bandwidth product	f _T	1.4	3.5	_	GHz	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	_	0.9	1.5	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Conversion gain	CG	_	15	_	dB	$V_{cc} = 6 \text{ V}, I_c = 2 \text{ mA},$ f = 900 MHz, $f_{osc} = 930 \text{ MHz (0dBm)},$ $f_{out} = 30 \text{ MHz}$
Noise figure	NF	_	9	_	dB	$V_{cc} = 6 \text{ V}, I_c = 2 \text{ mA},$ f = 900 MHz, $f_{osc} = 930 \text{ MHz (0dBm)},$ $f_{out} = 30 \text{ MHz}$
Oscillating output voltage	V _{osc}	_	140	_	mV	$V_{cc} = 6 \text{ V}, I_c = 5 \text{ mA},$ f = 930 MHz

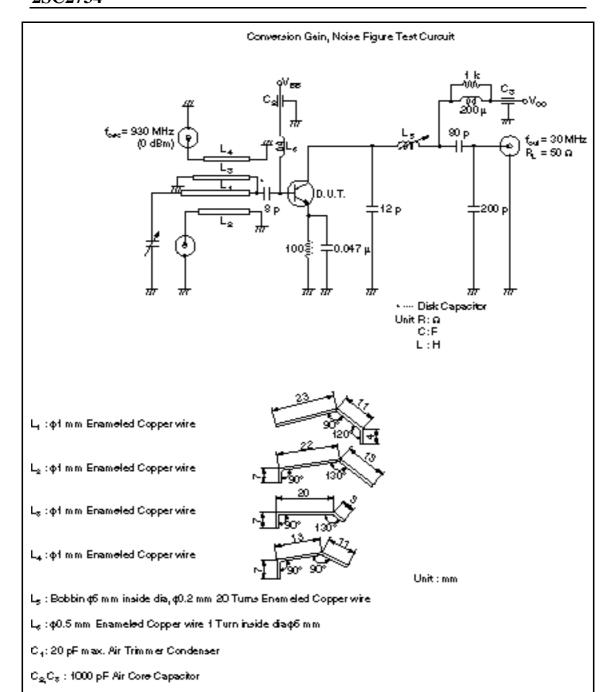
Note: Marking is "GC".

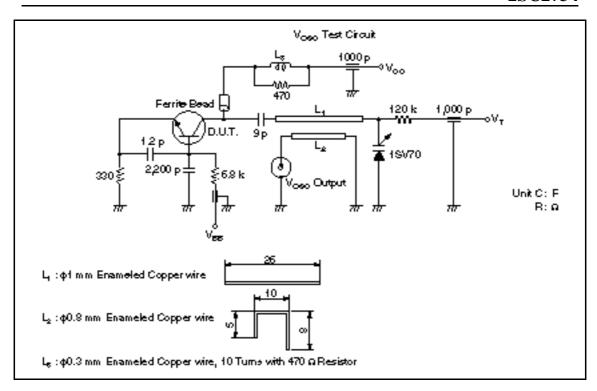


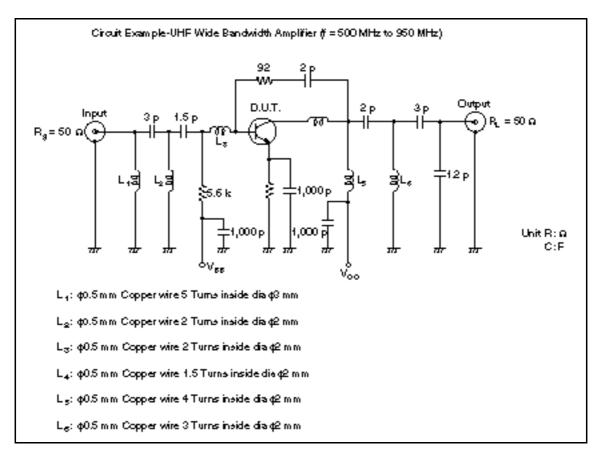
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